NPN SILICON SIGNAL
HIGH CURRENT GENERAL PURPOSE AMPLIFIERS AND SWITCHES
TO-18 PACKAGE

Type	h_{FE} @ 2V, 2mA	V_{CEO} @ 10mA Min. (V)	$V_{CE(sat)}$ @ 500mA, 50mA Max. (V)	P_T T_A=25°C (mW)	C_{cb} @ 10V Typical (pF)	f_t Typical (MHz)	PNP COMPLEMENT	Comments	Package Outline No.	Specification Sheet No.
2N5810	60-200 [5]	25	.75	500 [1,2]	9.4	150	2N5811	Excellent beta holdup of wide range of collector currents. Heatsinked versions [2] and complementary PNP's available. Excellent as audio drivers and outputs.	175	40.88
2N5812	150-500 [6]					165	2N5813			
2N5814	60-120	40				150	2N5815			40.89
2N5816	100-200					165	2N5817			
2N5818	150-300					180	2N5819			
2N5820	60-120	60				150	2N5821			40.90
2N5822	100-200					165	2N5823			
2N6010	100-300 [3]	40	.250 [4]	500 [1,2]	9.4	150	2N6011	General purpose device designed primarily for high level linear amplifiers, medium speed switching and control applications. Excellent beta linearity up to 800mA. Heatsink versions and complements available.	175	40.97
2N6012	250-500 [3]					180	2N6013			
2N6014	100-300 [3]	60				150	2N6015			40.100
2N6016	250-500 [3]					180	2N6017			

[1] P_T at T_C=25°C, 1000mW
[2] All units available with heatsink which raises P_T to 700mW, T_A=25°C; to specify a heatsink, substitute "HS" for "2N" in part no. Example: 2N5810 with heatsink is an HS5810. See page 20.
[3] h_{FE} measured at V_{CE}=1V, I_C=10mA
[4] $V_{CE(sat)}$ measured at I_C=300mA, I_B=30mA
[5] 45 min h_{FE} @ V_{CE}=2V, I_C=500mA
[6] 60 min h_{FE} @ V_{CE}=2V, I_C=500 mA

PNP SILICON SIGNAL
GENERAL PURPOSE SMALL SIGNAL AMPLIFIERS AND SWITCHES
TO-18 PACKAGE

Type	h_{FE} @ −1V −10mA	V_{CEO} @ −10mA Min. (V)	$V_{CE(sat)}$ @ −10mA −1mA Max. (V)	P_T T_A=25°C (mW)	C_{cb} @ −10V 1MHz Max. (pF)	f_t Typical (MHz)	Comments	Package Outline No.	Specification Sheet No.
2N6001	100-300	−25	−.100	400	8.0	340	Ideal for general purpose amplifiers, high speed switching, and low noise applications. Excellent beta linearity from 10uA to 300 mA as well as guaranteed NF and switching times. NPN complements available as 2N6000, 2N6002, 2N6004, 2N6006.	175	40.94
2N6003	230-500					400			
2N6005	100-300	−40				340			40.96
2N6007	250-500					400			
GET3638	20 min [1]	−25V	−.250 [2]	400	8.0	150	Epoxy replacements for 2N3638 and 2N3638A. General purpose amplifier and medium speed switch.	175	41.22
GET3638A	100 min [1]								

[1] h_{FE} @ V_{CE}=−10V, I_C=−10mA
[2] $V_{CE(sat)}$ @ I_C=−50mA, I_B=−2.5mA

PNP SILICON SIGNAL
HIGH SPEED SWITCHES
TO-18 PACKAGE

Type	h_{FE} @ −10V −150mA	V_{CEO} @ −10mA Min. (V)	$V_{CE(sat)}$ @ −150mA −15mA Max. (V)	P_T T_A=25°C (mW)	C_{cb} @ −10V 1MHz Max. (pF)	f_t Typical (MHz)	t_{on} MAX (nsec)	t_{off} MAX (nsec)	Comments	Package Outline No.	Specification Sheet No.
GET2904	40-120	−40	−0.4	400	8	200	50 [1]	110 [1]	Epoxy replacements for 2N2904, 2N2905, 2N2906, 2N2907. GET2904 and GET2905 are lead formed to TO-5 pin circle.	175	45.67
GET2906											
GET2905	100-300					250					45.68
GET2907											

[1] max switching times @ I_C=−150mA, I_{B_1}=I_{B_2}=−15mA